

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

NOV 08 2006

ATTY DOCKET NO.
ITO.0549US (P16246)

SERIAL NO.
10/634,146

APPLICANT(S):
BRIAN G. JOHNSON

FILING DATE:
August 4, 2003

GROUP ART UNIT:
2827

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.						
B.						
C.						
D.						
E.						
F.						

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
G.							
H.							
I.							
J.							
K.							
L.							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

MJW	M.	Horii, H., Yi, J.H., Park, J.H., Ha, Y.H., Baek, I.G., Park, S.O., Hwang, Y.N., Lee, S.H., Kim, Y.T., Lee, K.H., Chung, U-In and Moon, J.T., "A Novel Cell Technology Using N-doped GeSbTe Films for Phase Change RAM," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003
	N.	
	O.	
	P.	
	Q.	
	R.	
	S.	

EXAMINER

/Michael Weinberg/

DATE CONSIDERED

11/20/2006

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.